

# **R6007KNJ**

## Nch 600V 7A Power MOSFET

V <sub>DSS</sub>	600V
R <sub>DS(on)</sub> (Max.)	0.62Ω
Ι <sub>D</sub>	±7A
P <sub>D</sub>	78W



## Inner circuit



## Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	24
	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	R6007KNJ

## Application

Features

1) Low on-resistance.

3) Parallel use is easy.

2) Ultra fast switching speed.

4) Pb-free lead plating ; RoHS compliant

Switching

## • Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V <sub>DSS</sub>	600	V
Continuous drain current ( $T_c = 25$	5°C)	I <sub>D</sub> *1	±7	А
Pulsed drain current		$I_{DP}^{*2}$	±21	А
	static		±20	V
Gate - Source voltage	AC(f>1Hz)	V <sub>GSS</sub>	±30	V
Avalanche current, single pulse		I <sub>AS</sub>	1.3	А
Avalanche energy, single pulse		E <sub>AS</sub> *3	133	mJ
Power dissipation $(T_c = 25^{\circ}C)$	P <sub>D</sub>	78	W	
Junction temperature	Tj	150	°C	
Operating junction and storage te	T <sub>stg</sub>	-55 to +150	°C	

#### Thermal resistance

Deremeter	Cumph of	Values			Linit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}^{*4}$	-	-	1.6	°C/W
Thermal resistance, junction - ambient	$R_{thJA}^{*5}$	-	-	80	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	°C

## •Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Sumbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.		
Drain - Source breakdown voltage	$V_{(BR)DSS}$ $V_{GS} = 0V, I_D = 1mA$		600	-	-	V	
		V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V					
Zero gate voltage drain current	I <sub>DSS</sub>	$T_j = 25^{\circ}C$	-	-	100	μA	
		T <sub>j</sub> = 125°C	-	-	1000		
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20V, $V_{DS}$ = 0V	-	-	±100	nA	
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	3	-	5	V	
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.4A					
Static drain - source on - state resistance	R <sub>DS(on)</sub> *6	$T_j = 25^{\circ}C$	-	0.57	0.62	Ω	
		$T_j = 125^{\circ}C$	-	1.20	-		
Gate resistance	R <sub>G</sub>	f = 1MHz, open drain	-	3.2	-	Ω	



## • Electrical characteristics (T<sub>a</sub> = 25°C)

Deremeter	C: mah al	Conditions		Linit			
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Forward Transfer Admittance	Y <sub>fs</sub>  * <sup>6</sup>	<sup>*6</sup> V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.5A		3.8	-	S	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	470	-		
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25V	-	440	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	20	-		
Turn - on delay time	t <sub>d(on)</sub> *6	$V_{DD} \simeq 300$ V, $V_{GS}$ = 10V	-	18	-		
Rise time	t <sub>r</sub> *6	I <sub>D</sub> = 3.5A	-	22	-		
Turn - off delay time	t <sub>d(off)</sub> *6	$R_L \simeq 86.6\Omega$	-	35	-	ns	
Fall time	t <sub>f</sub> *6	R <sub>G</sub> = 10Ω	-	25	-		

## • Gate charge characteristics (T<sub>a</sub> = 25°C)

Deremeter	Cump of	Conditions		l lucit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	$Q_g^{*6}$	V <sub>DD</sub> ≃ 300V	-	14.5	-	
Gate - Source charge	Q <sub>gs</sub> *6	I <sub>D</sub> = 7A	-	4.2	-	nC
Gate - Drain charge	Q <sub>gd</sub> *6	V <sub>GS</sub> = 10V	-	5.8	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} \simeq 300V$ , $I_D = 7A$	-	6.8	-	V

\*1 Limited only by maximum channel temperature allowed.

- \*2 Pw  $\leq$  10µs, Duty cycle  $\leq$  1%
- \*3 L $\doteqdot$ 100mH, V<sub>DD</sub>=50V, R<sub>G</sub>=25 $\Omega$ , STARTING T<sub>i</sub>=25°C
- \*4 T<sub>C</sub>=25°C
- \*5 Mounted on a epoxy PCB FR4 (25mm x 27mm x 0.8mm)
- \*6 Pulsed



## •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Sympol	Conditions		Unit			
	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Continuous forward current	۱ <sub>S</sub> *1	T - 25°0	-	-	7	А	
Pulse forward current	ا <sub>SP</sub> *2	T <sub>C</sub> = 25°C	-	-	21	А	
Forward voltage	$V_{SD}^{*6}$	V <sub>GS</sub> = 0V, I <sub>S</sub> = 7.0A	-	-	1.5	V	
Reverse recovery time	t <sub>rr</sub> *6		-	302	-	ns	
Reverse recovery charge	Q <sub>rr</sub> *6	I <sub>S</sub> = 7A di/dt = 100A/µs	-	2.8	-	μC	
Peak reverse recovery current	۲ <sub>rrm</sub> *6		-	18	-	А	

## • Typical transient thermal characteristics

Symbol	Value	Unit	-	Symbol	Value	Unit
R <sub>th1</sub>	0.172		-	$C_{th1}$	0.00102	
R <sub>th2</sub>	0.694	K/W	-	$C_{th2}$	0.00288	Ws/K
R <sub>th3</sub>	0.640		-	$C_{\text{th}3}$	0.153	





## • Electrical characteristic curves



Fig.1 Power Dissipation Derating Curve



Fig.2 Maximum Safe Operating Area







#### •Electrical characteristic curves



Fig.4 Typical Output Characteristics(I)

Fig.5 Typical Output Characteristics(II)



#### • Electrical characteristic curves



#### Fig.6 Breakdown Voltage vs. Junction Temperature

Fig.7 Typical Transfer Characteristics



Fig.8 Gate Threshold Voltage vs. Junction Temperature





## Fig.9 Forward Transfer Admittance vs. Drain Current





Fig.11 Static Drain - Source On - State

## •Electrical characteristic curves



Fig.10 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Fig.12 Static Drain - Source On - State Resistance vs. Drain Current(I)





## •Electrical characteristic curves



Fig.13 Typical Capacitance vs. Drain - Source Voltage

## Fig.14 Switching Characteristics

## Fig.15 Dynamic Input Characteristics





## • Electrical characteristic curves



# Fig.16 Inverse Diode Forward Current vs. Source - Drain Voltage

Fig.17 Reverse Recovery Time vs. Inverse Diode Forward Current



#### Measurement circuits

#### Fig.1-1 Switching Time Measurement Circuit



Fig.2-1 Gate Charge Measurement Circuit



Fig.3-1 Avalanche Measurement Circuit



Fig.4-1 dv/dt Measurement Circuit



Fig.5-1 dv/dt Measurement Circuit



Fig.1-2 Switching Waveforms



Fig.2-2 Gate Charge Waveform



#### Fig.3-2 Avalanche Waveform



## Fig.4-2 dv/dt Waveform



Fig.5-2 dv/dt Waveform





#### Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES	
	MIN	MAX	MIN	MAX	
A1	0.00	0.30	0.000	0.012	
A2	4.30	4.70	0.169	0.185	
A3	0.25		0.0	10	
b	0.68	0.98	0.027	0.039	
b2	8.	90	0.3	50	
b3	1.14	1.44	0.045	0.057	
С	0.30	0.60	0.012	0.024	
c1	1.10	1.50	0.043	0.059	
D	9.80	10.40	0.386	0.409	
E	8.80	9.20	0.346	0.362	
е	2.	54	0.1	00	
HE	12.80	13.40	0.504	0.528	
L	2.70	3.30	0.106	0.130	
L1	0.90	1.50	0.035	0.059	
L2	1.	10	0.043		
L3	7.	25	0.285		
L4	1.	00	0.0	39	
Lp	0.90	1.50	0.035	0.059	
х	-	0.25	-	0.010	
DIM	MILIMETERS		INC	HES	
	MIN	MAX	MIN	MAX	
b5	-	1.23	-	0.049	
b6	-	10.40	-	0.409	
11	-	2.10	-	0.083	
12	-	7.55	-	0.297	
13	-	13.40		0.528	

Dimension in mm/inches





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## R6007KNJ - Web Page

**Distribution Inventory** 

Part Number	R6007KNJ
Package	LPTS(D2PAK)
Unit Quantity	1000
Minimum Package Quantity	1000
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes